

AOS Semiconductor Product Reliability Report

AOTF11C60, rev B

Plastic Encapsulated Device

ALPHA & OMEGA Semiconductor, Inc www.aosmd.com



This AOS product reliability report summarizes the qualification result for AOTF11C60. Accelerated environmental tests are performed on a specific sample size, and then followed by electrical test at end point. Review of final electrical test result confirms that AOTF11C60 passes AOS quality and reliability requirements.

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I. Product Description:

The AOTF11C60 is fabricated using an advanced high voltage MOSFET process that is designed to deliver high levels of performance and robustness in popular AC-DC applications. By providing low RDS(on), Ciss and Crss along with guaranteed avalanche capability this parts can be adopted quickly into new and existing offline power supply designs.

For Halogen Free add "L" suffix to part number: AOTF11C60L

Details refer to the datasheet.

II. Die / Package Information:

AOTF11C60

Process Standard sub-micron

600V N-Channel MOSFET

Package TypeTO220FLead FrameBare CuDie AttachSoft solderBondingAl wire

Mold Material Epoxy resin with silica filler

Moisture Level Up to Level 1 *

Note * based on info provided by assembler and mold compound supplier



III. Result of Reliability Stress for AOTF11C60

Test Condition	Time Point	Lot Attribution	Total Sample size	Number of Failures	Reference Standard
168hr 85°c /85%RH +3 cycle reflow@250°c	-	12 lots	2112pcs	0	JESD22- A113
Temp = 150°c , Vgs=100% of Vgsmax	168hrs 500 hrs 1000 hrs	3 lots 4 lots	539pcs 77 pcs / lot	0	JESD22- A108
Temp = 150°c , Vds=80% of Vdsmax	168hrs 500 hrs 1000 hrs	3 lots 4 lots	539pcs 77 pcs / lot	0	JESD22- A108
130°c , 85%RH, 33.3 psi, Vgs = 100% of Vgs max	96 hrs	9 lots (Note A*)	495pcs 55 pcs / lot	0	JESD22- A110
121°c , 29.7psi, RH=100%	96 hrs	9 lots (Note A*)	693pcs 77 pcs / lot	0	JESD22- A102
-65°c to 150°c , air to air,	250 / 500 cycles	12 lots	924pcs	0	JESD22- A104
	168hr 85°c /85%RH +3 cycle reflow@250°c Temp = 150°c, Vgs=100% of Vgsmax Temp = 150°c, Vds=80% of Vdsmax 130°c, 85%RH, 33.3 psi, Vgs = 100% of Vgs max 121°c, 29.7psi, RH=100%	Point 168hr 85°c /85%RH +3 cycle reflow@250°c Temp = 150°c, Vgs=100% of Vgsmax Temp = 150°c, Vds=80% of Vdsmax 130°c, 85%RH, 33.3 psi, Vgs = 100% of Vgs max 121°c, 29.7psi, RH=100% -65°c to 150°c, 250 / 500	Point	Point Attribution Sample size	Point Attribution Sample size of Failures

IV. Reliability Evaluation

FIT rate (per billion): 4.16 MTTF = 27426 years

The presentation of FIT rate for the individual product reliability is restricted by the actual burn-in sample size of the selected product (AOTF11C60). Failure Rate Determination is based on JEDEC Standard JESD 85. FIT means one failure per billion hours.

Failure Rate (FIT) =
$$\text{Chi}^2 \times 10^9 / [2 \text{ (N) (H) (Af)}]$$

= 1.83 x 10⁹ / [2x (6x77x500 +8x77x1000) x259] = 4.16
MTTF = $10^9 / \text{FIT} = 2.40 \times 10^8 \text{hrs} = 27426 \text{ years}$

 Chi^2 = Chi Squared Distribution, determined by the number of failures and confidence interval N = Total Number of units from HTRB and HTGB tests

H = Duration of HTRB/HTGB testing

Af = Acceleration Factor from Test to Use Conditions (Ea = 0.7eV and Tuse = 55°C)

Acceleration Factor [Af] = Exp [Ea/k (1/Tj u - 1/Tj s)]

Acceleration Factor ratio list:

	55 deg C	70 deg C	85 deg C	100 deg C	115 deg C	130 deg C	150 deg C
Af	259	87	32	13	5.64	2.59	1

Tj s = Stressed junction temperature in degree (Kelvin), K = C+273.16

Tj u =The use junction temperature in degree (Kelvin), K = C+273.16

 \mathbf{k} = Boltzmann's constant, 8.617164 x 10⁻⁵eV / K